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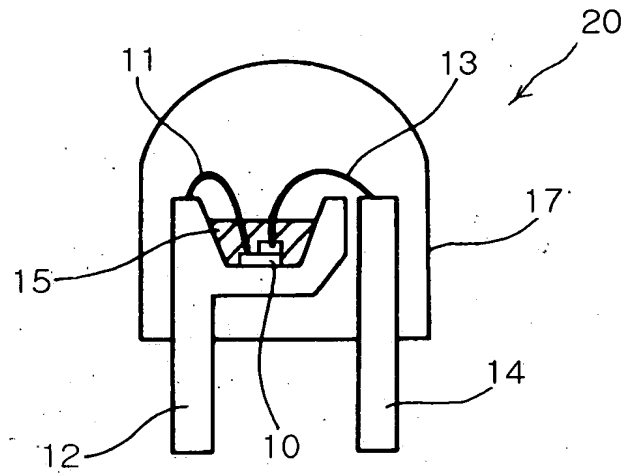


FIG. 1a  
PRIOR ART

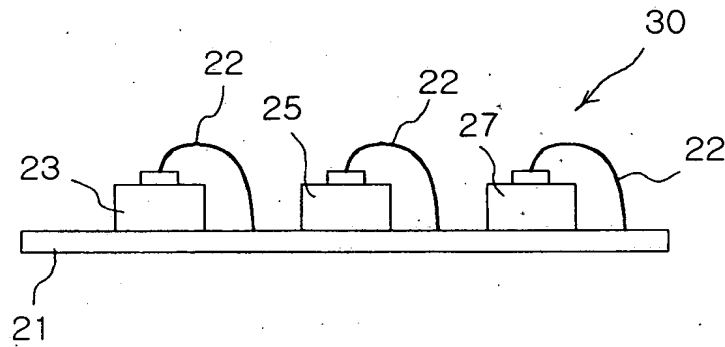


FIG. 1b  
PRIOR ART

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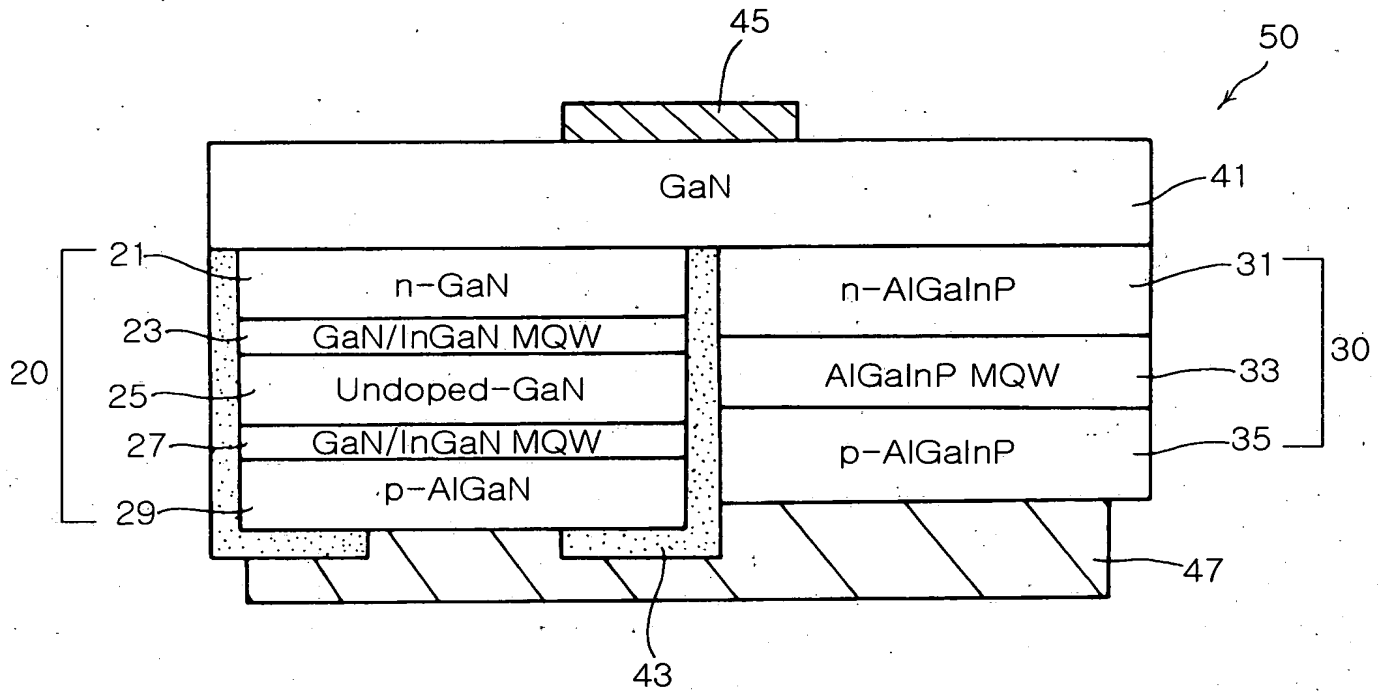


FIG. 2

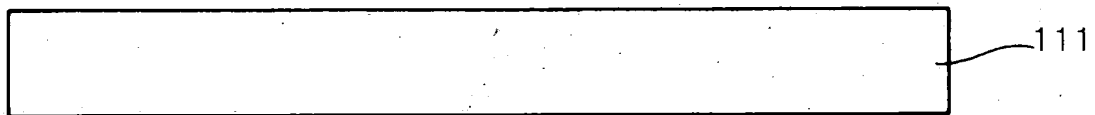


FIG. 3a

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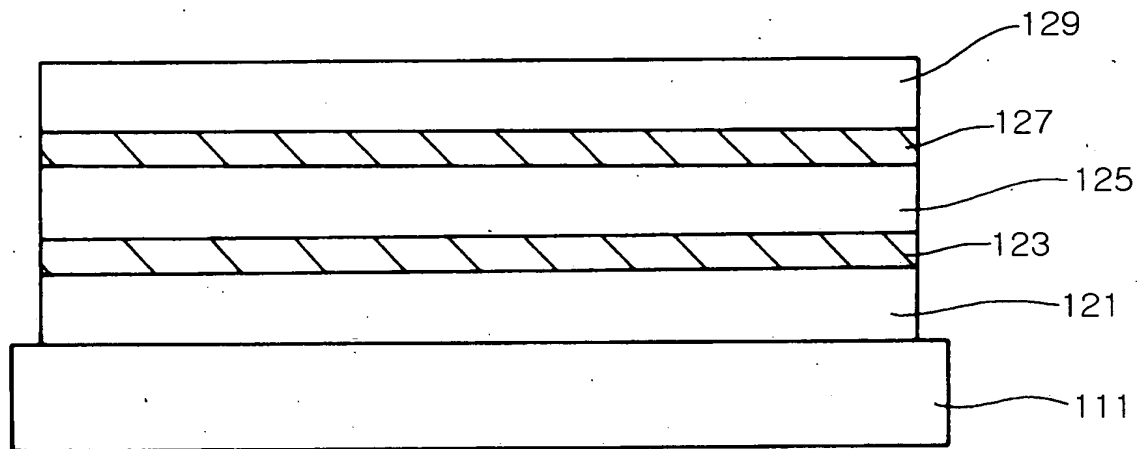


FIG. 3b

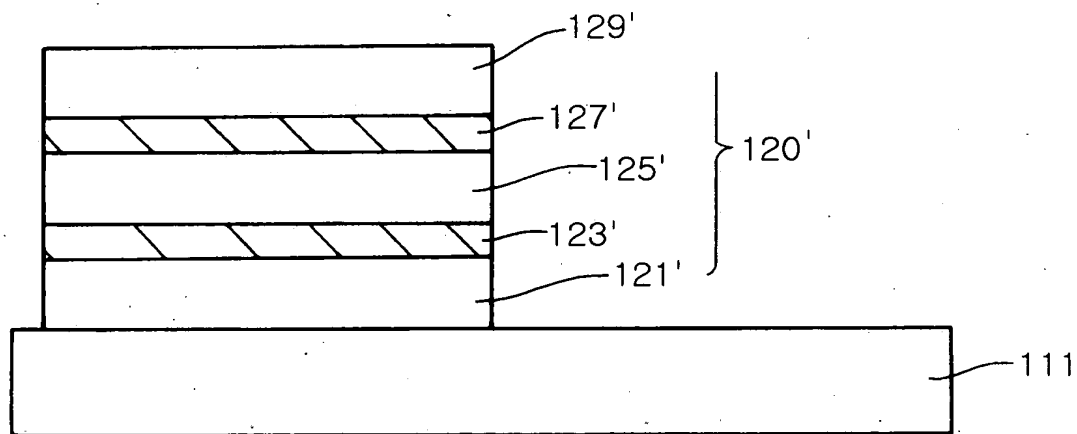


FIG. 3c

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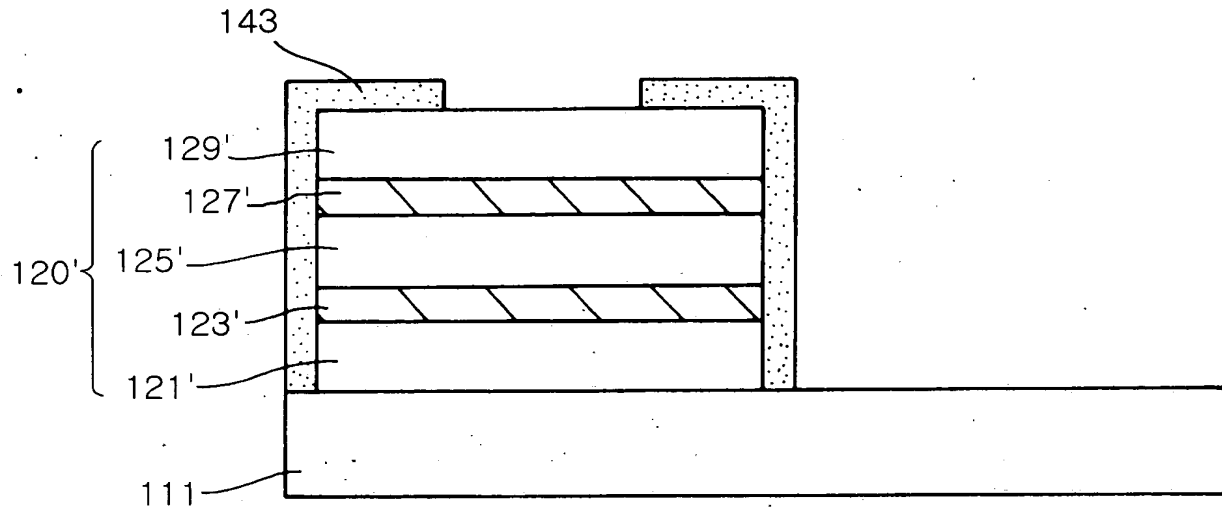


FIG. 3d

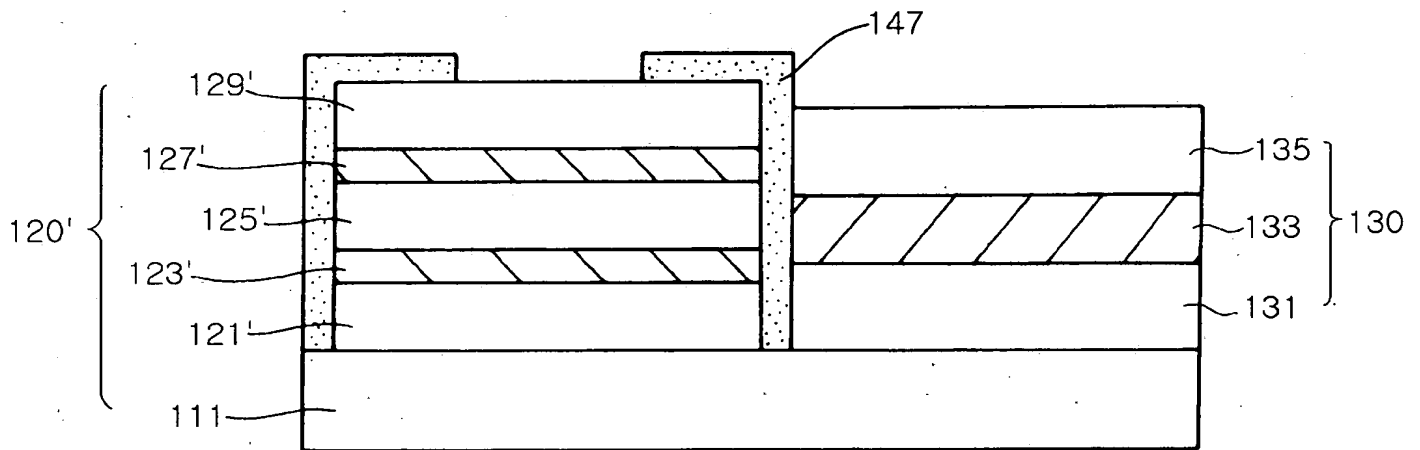


FIG. 3e

A cross-sectional view of a semiconductor device 200. The device features a substrate 151 with a top layer 181 and a bottom layer 183. A central region 170 is defined by a U-shaped structure 187. A vertical structure 185 is located on the top surface of the central region. A vertical structure 194 is located on the left side of the device, with a positive terminal (+) indicated. A vertical structure 195 is located on the right side of the device, with a negative terminal (-) indicated. A horizontal structure 160a is located on the left side of the central region, and a horizontal structure 160b is located on the right side of the central region. The entire device is labeled 200.

FIG. 4

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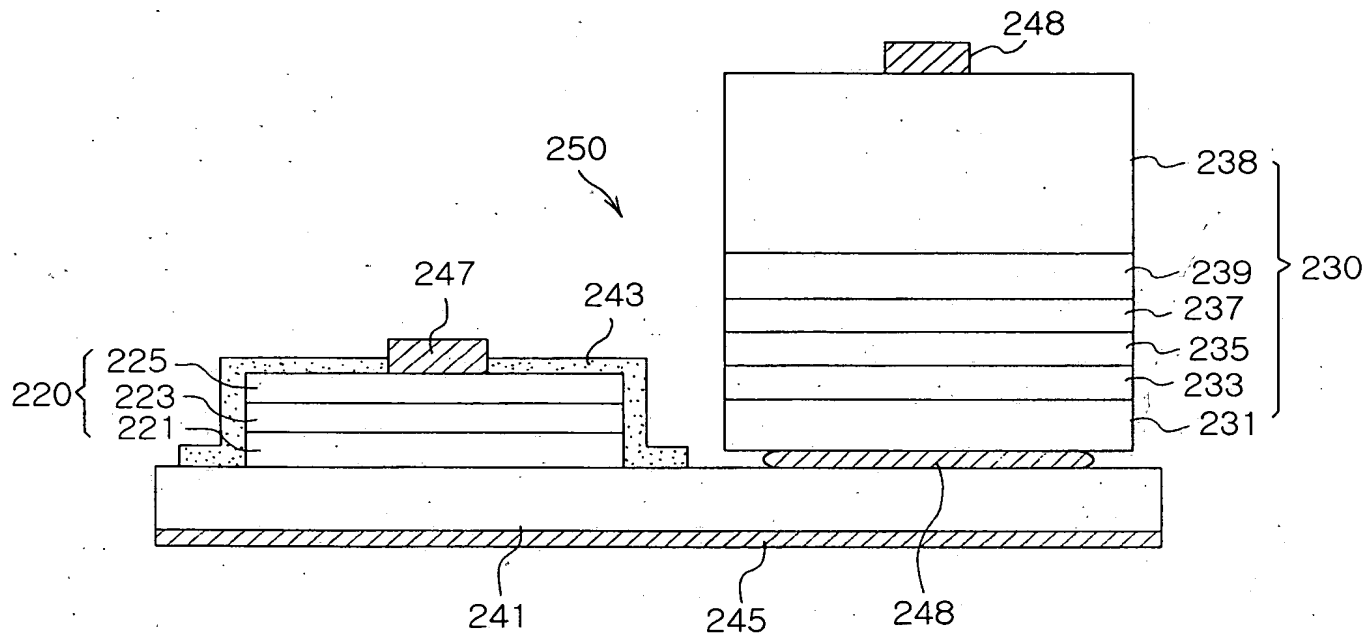


FIG. 5

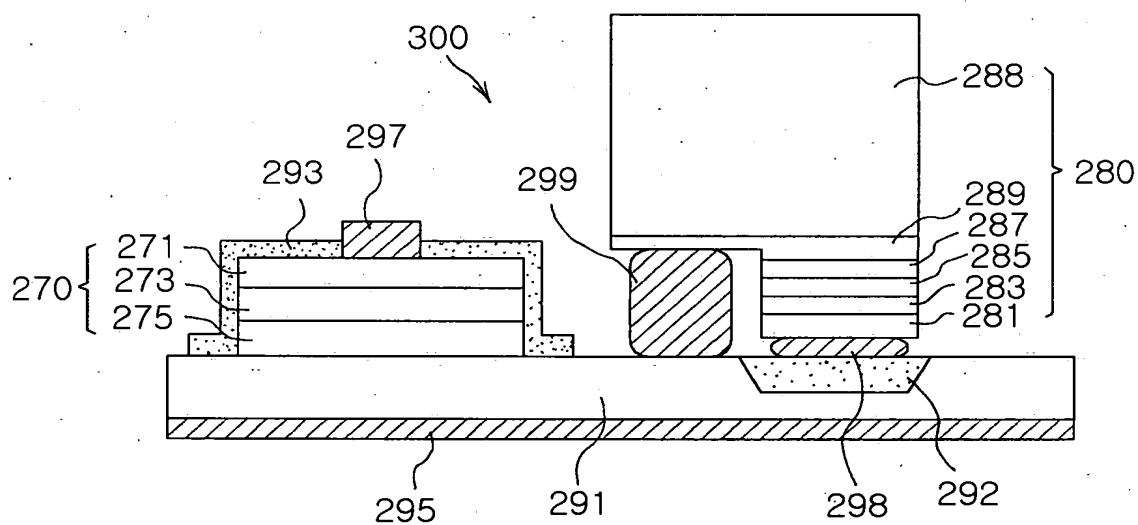


FIG. 6